



1. This question is compulsory. You should attempt all six parts. State clearly any assumptions made in your calculations.

- a) For the circuit in Figure 1.1, determine the operating mode of the MOSFET and the value of the voltage  $V$ .

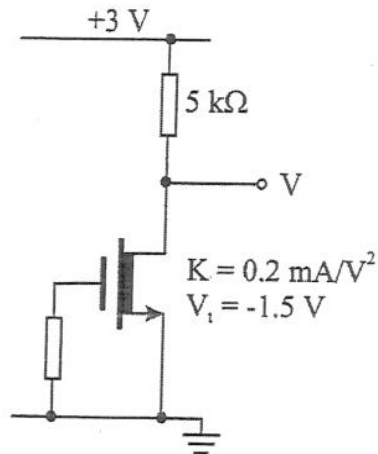


Figure 1.1

[6]

- b) For the circuit in Figure 1.2, determine the operating modes of both transistors and the value of the current  $I$ .

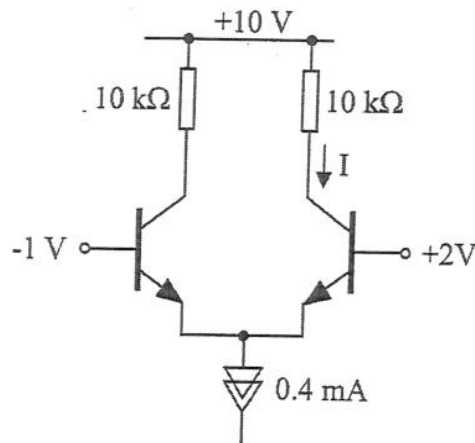


Figure 1.2

[6]

- c) A grounded common emitter amplifier is constructed using a BJT with an Early voltage of 90 V. If the load resistance in the collector circuit is 10 kΩ, and the transistor is biased at a collector current of 0.5 mA, what is the small-signal voltage gain of the circuit?

[6]

Question 1 continues on the next page...

- d) Figure 1.3 shows an enhancement mode MOSFET connected as a 2-terminal component. Sketch the I-V characteristic of this device for  $V \geq 0$ , marking on your graph any boundaries between different operating modes.

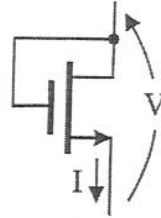


Figure 1.3

[6]

- e) The voltage  $V_{IN}$  in Figure 1.4 changes to +5V at time  $t = 0$ , after having been held at zero for a long time. Calculate the time  $T$  taken for the output voltage  $V_{OUT}$  to fall to 5% of its initial value, and sketch the time variation of  $V_{OUT}$  from just before  $t = 0$  to time  $t = 2T$ .

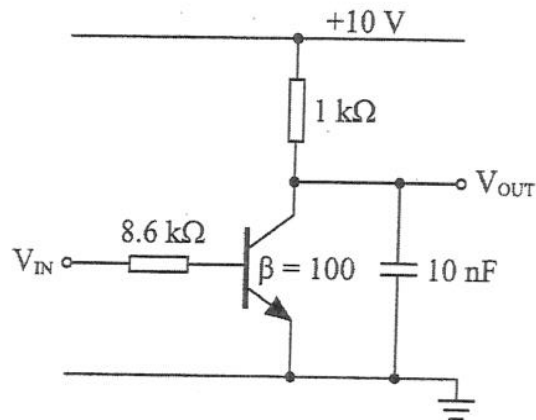


Figure 1.4

[10]

- f) The characteristic equation for a Colpitts oscillator is of the form:

$$s^3 LC_1 C_2 + \frac{s^2 LC_2}{R} + s(C_1 + C_2) + \left( g_m + \frac{1}{R} \right) = 0$$

where  $L$ ,  $C_1$  and  $C_2$  are the reactive components,  $R$  represents the circuit losses, and  $g_m$  is the usual transistor parameter. By assuming an appropriate form for the complex frequency,  $s$ , derive an expression for the oscillation frequency. Also determine the minimum transconductance required for oscillation to occur.

[6]

2. a) Determine the collector bias current and quiescent output voltage for the amplifier in Figure 2.1, stating clearly any assumptions you make. Your calculation should take into account the base current of the transistor. [8]
- b) Draw a small-signal equivalent circuit for the amplifier, assuming the bypass capacitor is effectively short-circuit, and hence determine the small-signal macromodel parameters (input resistance, output resistance and voltage gain) in the mid-band. [12]
- c) Two amplifiers similar to that in Figure 2.1 are cascaded and inserted between a signal source and a load, as shown in Figure 2.2. Determine the overall voltage gain  $v_L/v_S$  for this arrangement at frequencies for which all the coupling capacitors are effectively short-circuit. [10]

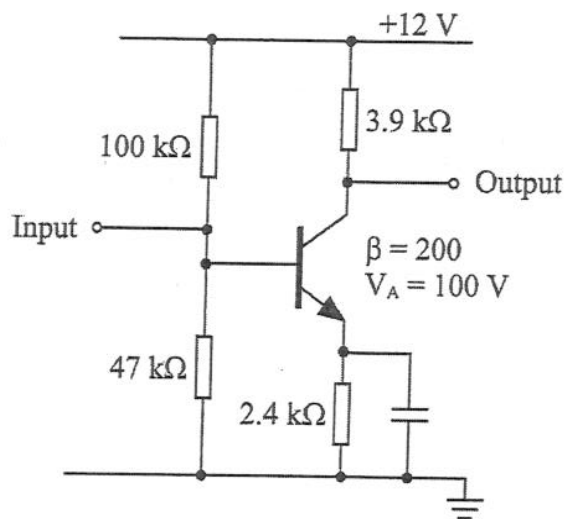


Figure 2.1

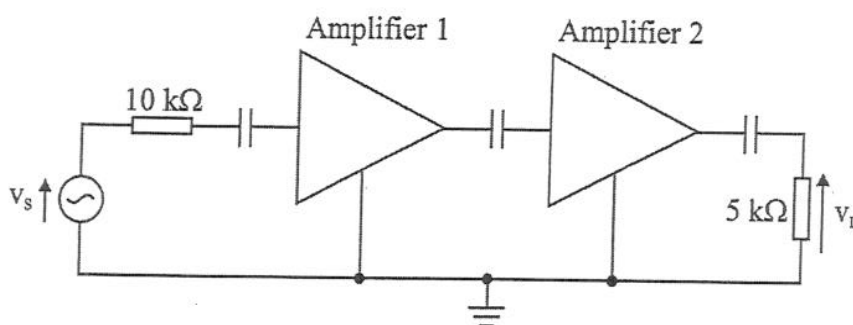


Figure 2.2

3. Figure 3.1 shows an NMOS amplifier employing two enhancement mode MOSFETs.

- a) Neglecting the current in the resistor  $R_F$ , and assuming both transistors are active, show that the output voltage  $V_{OUT}$  may be expressed as:

$$V_{OUT} = V_{DD} - V_{t2} - \sqrt{\frac{K_1}{K_2}} \cdot (V_{G1} - V_{t1})$$

where  $K$  and  $V_t$  denote the usual MOSFET parameters,  $V_G$  denotes gate voltage, and subscripts 1 and 2 refer to Q1 and Q2 respectively. [10]

- b) Determine the range of output voltages over which both transistors will remain in the active region, and choose the value of  $R_F$  so that the quiescent output voltage lies exactly at the middle of this range. [12]

- c) Using the equation in part a), or otherwise, calculate the voltage gain of the amplifier in the mid-band where the input capacitor is effectively short-circuit. Would you expect this amplifier to show linear behaviour for large signals? Explain your answer. [8]

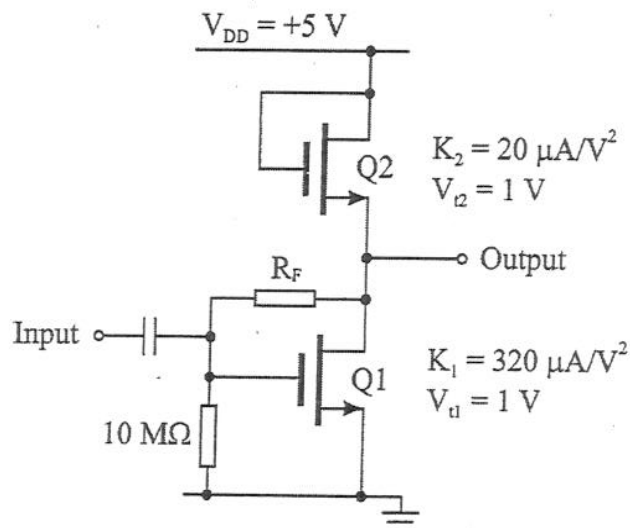


Figure 3.1

4. a) Sketch the circuit diagram for a Class B push-pull output stage. What are the main drawbacks of this configuration as a voltage follower? [10]
- b) Figure 4.1 shows one possible configuration for a Class AB output stage. In this circuit, Q2 and Q4 are matched, as are Q1 and Q3. All transistors have  $\beta = 50$ .

Explain the role of Q1 and Q3. Also, by considering just the upper half of the circuit and neglecting base currents, show that, when  $V_{out} = 0$ , the currents  $I_1$  and  $I_2$  are related as follows:

$$I_2 \exp(I_2 R / V_T) = N I_1$$

where  $N = I_{S2}/I_{S1}$  is the ratio of the saturation currents of Q2 and Q1, and  $V_T = 25$  mV. If  $I_{S1} = 0.25$  pA and  $I_{S2} = 5$  pA, what value of R will give a quiescent current of 10 mA in the output transistors? [15]

- c) Calculate the base-emitter voltage of Q2 when the output stage is delivering 100 mA into the load. In this calculation you should assume that Q4 is carrying negligible current. Also calculate the base-emitter voltages of Q1, Q3 and Q4 under these conditions, and hence verify that the assumption you made about Q4 is justified. [5]

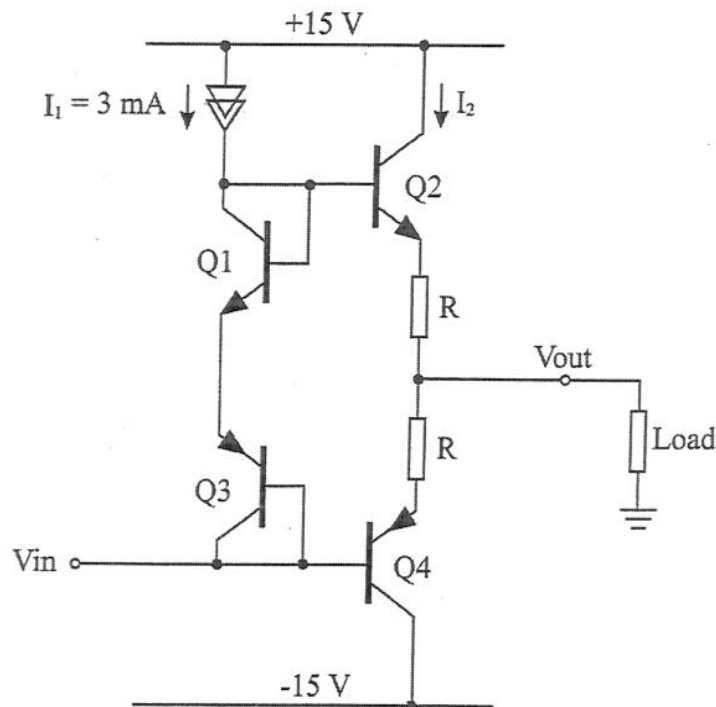


Figure 4.1

1a)  $I_G = 0$ , so  $V_{GS} = 0$  and (depletion) MOSFET is conducting  
If active then  $I_D = K(0 - V_t)^2 = 0.2 \times (1.5)^2 = 0.45 \text{ mA}$

This would imply  $V = 3 - 0.45 \times 5 = 0.75 \text{ V}$

But this inconsistent with active mode since  $0.75 < (0 - 1.5)$

$\Rightarrow$  MOSFET must be in TRIODE

$$\text{Now } I_D = 0.2 [2 \cdot (1.5) \cdot V - V^2] = \frac{3-V}{5}$$

$$\Rightarrow 3V - V^2 = 3 - V \Rightarrow V^2 - 4V + 3 = 0$$

$$\Rightarrow (V-1)(V-3) = 0. \quad V=3 \text{ rejected, so } \underline{V=1V} \quad [6]$$

b) Differential i/p voltage (3V) is  $\gg V_T$  so can assume  
RH transistor is carrying all the tail current.

$$V_E = \max\{2, -13 - 0.7\} = 1.3 \text{ V}$$

$\Rightarrow$  For LH transistor  $V_{BE} = -2.3 \text{ V}$ ,  $V_{CE} = +11 \text{ V} \Rightarrow$  LH CUT-OFF.

RH transistor has  $I_E = 0.4 \text{ mA}$ , so  $I = 0.4 \text{ mA}$  if  
active (neglecting  $I_B$ ). This implies  $V_C = 10 - 0.4 \times 10 = 6 \text{ V}$

Which is  $> V_E$  so active assumption OK.  $\Rightarrow$  RH ACTIVE [6]

c) Small-signal voltage gain for grounded C.E. amp  
is  $A_v = -g_m(R_C // r_o)$ . (standard result)

$$g_m = \frac{I_C}{V_T} = \frac{0.5 \text{ mA}}{25 \text{ mV}} = 0.02 \text{ S}$$

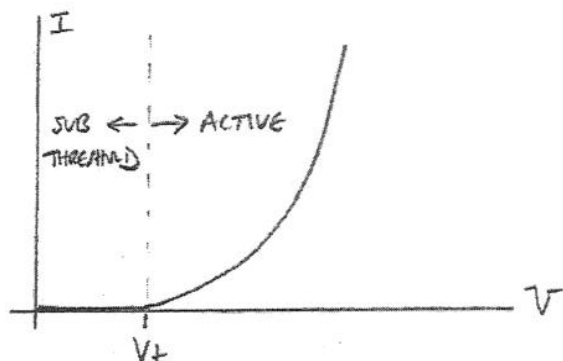
$$r_o = \frac{V_A}{I_C} = \frac{90 \text{ V}}{0.5 \text{ mA}} = 180 \text{ k} ; R_C = 10 \text{ k}$$

$$\Rightarrow A_v = -0.02 \times (180 \text{ k} // 10 \text{ k}) = \underline{-189} \quad [6]$$

d)  $I_G = 0$ , so  $I = I_D$ . Also,  $V_{GS} = V_{DS} = V$  so  
(enhancement) MOSFET is active provided  $V > V_t$

So  $I = 0$  for  $V \leq V_t$

$$I = K(V - V_t)^2 \text{ for } V > V_t$$

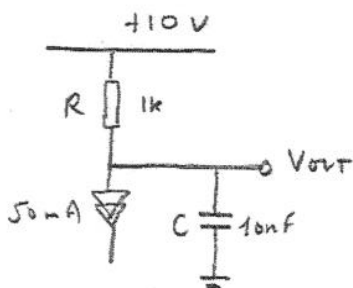


[6]

- 1 e) Before 1/μ step, cct has reached steady state with  $V_{out} = 10V$   
 Capacitor voltage is continuous so  $V_{out}|_{t=0^+} = +10V$   
 $\Rightarrow$  At  $t=0^+$  transistor is ACTIVE with

$$I_B = (5 - 0.7) / 8.6k = 500 \mu A ; I_C = 100 \times 500 \mu A = 50mA$$

Equivalent cct is :



If transistor remained active then new S.S. would be

$$V_{out} = 10 - 50 \times 1 = -40V$$

$\Rightarrow$  Using standard result, time variation of  $V_{out}$  while transistor

remains active is :

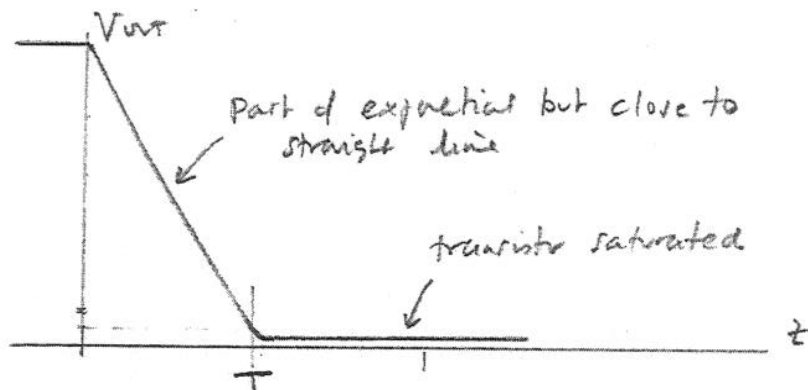
$$V_{out} = -40 + (10 - (-40)) e^{-t/\tau}$$

$$= -40 + 50 e^{-t/\tau} \quad \tau = RC = 10 \mu sec$$

Time taken for  $V_{out}$  to fall to 5% of +10V is

give by:  $0.5 = -40 + 50 e^{-T/\tau}$

or  $T = \tau \ln[50/40.5] = \underline{\underline{2.11 \mu sec}}$



[10]

- f) For stable oscillation, characteristic equation must have solution for which  $s = j\omega$ , where  $\omega$  is the oscillation frequency. Substituting this form for  $s$  gives

$$-j\omega^3 LC_1 C_2 - \frac{\omega^2 LC_2}{R} + j\omega(C_1 + C_2) + (g_m + \frac{1}{R}) = 0$$

Imag. part  $\Rightarrow \omega^2 = \frac{C_1 + C_2}{LC_1 C_2}$  or  $f = \frac{1}{2\pi} \sqrt{\frac{C_1 + C_2}{LC_1 C_2}}$  Hz

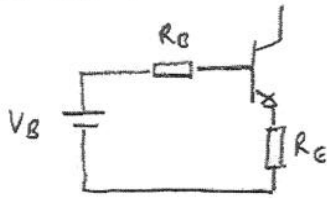
Real part  $\Rightarrow \frac{(C_1 + C_2)}{LC_1 C_2} \cdot \frac{LC_2}{R} = g_m + \frac{1}{R}$  or  $g_m = \frac{C_2}{C_1 R}$

This is the minimum  $g_m$  for oscillation

[6]



2 a) Bias ckt :



where  $V_B = \frac{47}{47+100} \times 12 = 3.837 \text{ V}$

and  $R_B = 100k \parallel 47k = 31.97 \text{ k}$

KVL:  $I_E R_E + V_{BE} + I_B R_B = V_B$

$\Rightarrow I_E = \frac{V_B - V_{BE}}{R_E + R_B/\beta}$

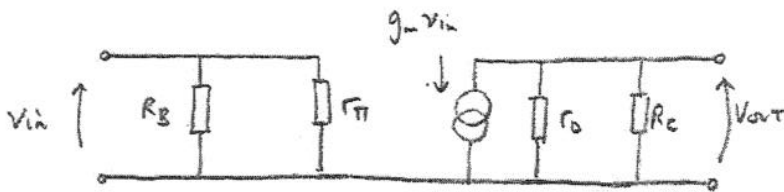
Assuming  $V_{BE} = 0.7 \Rightarrow I_E = 1.226 \text{ mA}$

$I_C = \alpha I_E = \frac{200}{201} \times 1.226 = 1.22 \text{ mA}$

$V_{out} = 12 - 1.22 \times 3.9 = 7.24 \text{ V}$

[8]

b) SSEC :



$g_m = I_C / V_T = 48.8 \text{ mS}$

$r_{\pi} = \beta / g_m = 4.098 \text{ k}\Omega$

$r_o = \frac{V_A}{I_C} = 81.97 \text{ k}\Omega$

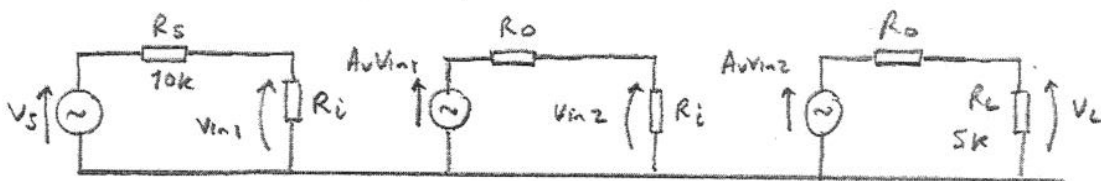
$R_i = R_B \parallel r_{\pi} = 31.97k \parallel 4.098k = 3.63 \text{ k}\Omega$

$R_o = R_C \parallel r_o = 3.9k \parallel 81.97k = 3.72 \text{ k}\Omega$

$A_v = -g_m R_o = -182$

[12]

c) Overall SSEC with s/c capr :



$V_L = \frac{R_L}{R_L + R_o} \cdot A_v V_{in2} = \frac{R_L}{R_L + R_o} \cdot A_v \cdot \frac{R_i}{R_i + R_o} \cdot A_v \cdot \frac{R_i}{R_i + R_s} \cdot V_s$

$\Rightarrow$  Overall gain  $\omega$

$\frac{V_L}{V_s} = A_v^2 \cdot \frac{R_L}{R_L + R_o} \cdot \frac{R_i}{R_i + R_o} \cdot \frac{R_i}{R_i + R_s}$

$= (-182)^2 \cdot \frac{5}{5+3.72} \cdot \frac{3.63}{3.63+3.72} \cdot \frac{3.63}{3.63+10} = 2498$  [10]

3 a) Assuming both transistors are active =

$$I_{D1} = K_1 (V_{G1} - V_{t1})^2 \quad ; \quad I_{D2} = K_2 (V_{DD} - V_{out} - V_{t2})^2$$

if current in  $R_F$  can be neglected, then  $I_{D1} = I_{D2}$

$$\Rightarrow K_1 (V_{G1} - V_{t1})^2 = K_2 (V_{DD} - V_{out} - V_{t2})^2$$

taking +ve  $\sqrt{\quad}$   $\Rightarrow \sqrt{\frac{K_1}{K_2}} (V_{G1} - V_{t1}) = V_{DD} - V_{out} - V_{t2}$

(both active)

$\Rightarrow$  required result after rearrangement [10]

b) Q2 is DG-connected  $\Rightarrow$  active provided  $V_{G5} > V_t$

Requires  $V_{DD} - V_{out} \geq V_{t2}$  or  $V_{out} \leq V_{DD} - V_{t2}$

$$V_{out} \leq 4V$$

Q1 active provided  $V_{out} \geq V_{G1} - V_{t1}$

Can get lower limit by substituting  $V_{out} = V_{G1} - V_{t1}$  into

part a) equation  $\Rightarrow V_{out} = \frac{V_{DD} - V_{t2}}{1 + \sqrt{K_1/K_2}} = \frac{4}{5} = 0.8V$

So, range is  $\underline{0.8V \leq V_{out} \leq 4V}$

Middle of range is  $+2.4V$ , which corresponds to a

$V_{G1}$  of  $\frac{5 - 1 - 2.4}{4} + 1 = 1.4V$

(rearranging part a) eqn)  $\rightarrow$

But at DC  $V_{G1} = \frac{10M}{10M + R_F} \times V_{out}$

$\Rightarrow \frac{R_F}{10M} = \frac{2.4}{1.4} - 1 = 0.714 \Rightarrow \underline{R_F = 7.14 M\Omega}$  [12]

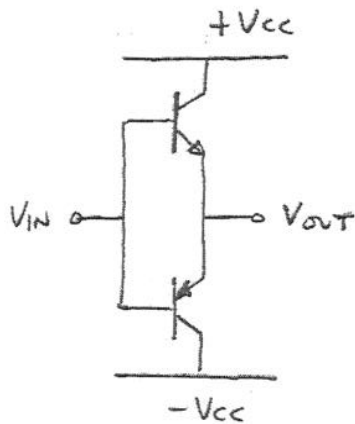
c) Can get gain simply by differentiating part a) eqn

i.e.  $A_v = \frac{\partial V_{out}}{\partial V_{in}} = \frac{\partial V_{out}}{\partial V_{G1}} = -\sqrt{\frac{K_1}{K_2}} = \underline{\underline{-4}}$

Yes, amplifier is linear for large signals because large-signal i/p-o/p relationship is linear in  $V_{G1}$ .

[8]

4 a)



Main drawbacks or voltage follower are cross-over distortion and level shift (that is different for +ve and -ve signals).

[10]

b) Q1 and Q3 provide a bias voltage between the bases of Q2 and Q4, ensuring that at least one of them is conducting at all times.

When  $V_{out} = 0$ ,  $V_{E1} = 0$  also because of symmetry.

KVL for Q1, Q2 and R then gives:

$$V_{BE1} = V_{BE2} + I_2 R$$

$$\Rightarrow V_T \ln\left(\frac{I_1}{I_{S1}}\right) = V_T \ln\left(\frac{I_2}{I_{S2}}\right) + I_2 R$$

$$\Rightarrow \frac{I_1}{I_{S1}} = \frac{I_2}{I_{S2}} \cdot \exp\left(\frac{I_2 R}{V_T}\right) \quad \text{or} \quad N I_1 = I_2 \exp\left(\frac{I_2 R}{V_T}\right) \quad \text{as req.}$$

Putting  $N = \frac{5}{0.25} = 20$ ,  $I_1 = 3 \text{ mA}$ ,  $I_2 = 10 \text{ mA} \Rightarrow \underline{\underline{R = 4.48 \Omega}}$  [15]

c)  $I_{E2} = 100 \text{ mA} \Rightarrow I_{C2} = 98 \text{ mA}$ ;  $I_{B2} = 1.96 \text{ mA}$

$$I_{C2} = I_{S2} \exp\left(\frac{V_{BE2}}{V_T}\right) \Rightarrow V_{BE2} = V_T \ln\left(\frac{I_{C2}}{I_{S2}}\right) = \underline{\underline{592 \text{ mV}}}$$

If  $I_{B2} = 1.96 \text{ mA}$ , then  $I_{C1} = 3 - 1.96 = 1.04 \text{ mA}$

and  $I_{C1} = 1.02 \text{ mA} \Rightarrow V_{BE1} = V_T \ln\left(\frac{I_{C1}}{I_{S1}}\right) = 553 \text{ mV} = V_{BE3}$

Now, working anti-clockwise around loop starting from  $V_{out}$  we get:

$$\begin{aligned} V_{BE4} &= V_{out} + I_{LOAD} R + V_{BE2} - V_{BE1} - V_{BE3} \\ &= V_{out} + 448 \text{ mV} + 592 \text{ mV} - 553 \text{ mV} - 553 \text{ mV} \\ &= V_{out} - 66 \text{ mV} \end{aligned}$$

So, with no current in lower "R", we have  $V_{BE4} = -66 \text{ mV}$

and  $I_{E4}$  is negligible  $\Rightarrow$  assumption was justified. [5]